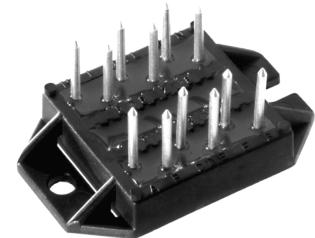
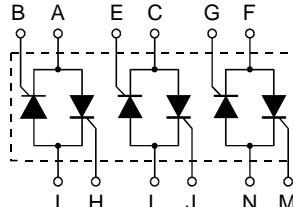


AC Controller Modules

I_{RMS} = 3x 35 A
V_{RRM} = 600-1200 V

Preliminary data

V _{RSM}	V _{RRM}	Type
V _{DSM}	V _{DRM}	
V	V	
700	600	VWO 35-06ho7
900	800	VWO 35-08ho7
1300	1200	VWO 35-12ho7



Symbol	Test Conditions	Maximum Ratings			Features
I _{RMS}	T _C = 85°C, (per phase)	35	A		
I _{TAVM}	T _C = 85°C; (180° sine ; per thyristor)	16	A		
I _{TSM}	T _{VJ} = 45°C; V _R = 0	200	A		• Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	210	A		• Soldering connections for PCB mounting
I ² t	T _{VJ} = T _{VJM} V _R = 0	180	A		• Isolation voltage 3000 V~
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	190	A		• Planar passivated chips
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 μs	200	A ² s		
	V _D = 2/3 V _{DRM} I _G = 0.15 A di _G /dt = 0.15 A/μs	150	A ² s		
(dv/dt) _{cr}	T _{VJ} = T _{VJM} R _{GK} = ∞; method 1 (linear voltage rise)	160	A ² s		
	V _{DRM} = 2/3 V _{DRM}	150	A ² s		
V _{RGM}		500	V/μs		
P _{GM}	T _{VJ} = T _{VJM}	10	V		
	I _T = I _{TAVM}	t _p = 30 μs t _p = 300 μs	≤ 5 ≤ 2.5 0.5	W	
P _{GAVM}		-40...+125	°C		
T _{VJ}		125	°C		
T _{VJM}		-40...+125	°C		
T _{stg}					
V _{ISOL}	50/60 Hz, RMS	t = 1 min	2500	V~	
	I _{ISOL} ≤ 1 mA	t = 1 s	3000	V~	
M _d	Mounting torque (M4)	1.5 - 2 14 - 18	Nm lb.in.		
Weight	typ.	18	g		

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
 IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	≤	5	mA
V_T	$I_T = 20 \text{ A}; T_{VJ} = 25^\circ\text{C}$	≤	1.6	V
V_{TO}	For power-loss calculations only	0.85	V	
r_T		27	$\text{m}\Omega$	
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	≤	1.5	V
	$T_{VJ} = -40^\circ\text{C}$	≤	2.5	V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	≤	25	mA
	$T_{VJ} = -40^\circ\text{C}$	≤	50	mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤	0.2	V
I_{GD}		≤	3	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.1 \text{ A}; di_G/dt = 0.1 \text{ A}/\mu\text{s}$	≤	75	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	≤	50	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.1 \text{ A}; di_G/dt = 0.1 \text{ A}/\mu\text{s}$	≤	2	μs
R_{thJC}	per thyristor; DC	1.3	K/W	
	per module	0.22	K/W	
R_{thJK}	per thyristor; DC	1.8	K/W	
	per module	0.3	K/W	
d_s	Creeping distance on surface	11.2	mm	
d_A	Creepage distance in air	5.0	mm	
a	Max. allowable acceleration	50	m/s^2	

Dimensions in mm (1 mm = 0.0394")

